September 2000

FDS9926A

FAIRCHILD

Dual N-Channel 2.5V Specified PowerTrench[®] MOSFET

General Description

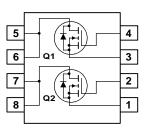
These N-Channel 2.5V specified MOSFETs use Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V - 10V).

Applications

- Battery protection
- Load switch
- Power management



- 6.5 A, 20 V. $R_{DS(ON)} = 0.030 \ \Omega \ @ V_{GS} = 4.5 \ V$ $R_{DS(ON)} = 0.043 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Optimized for use in battery protection circuits
- + $\pm 10~V_{GSS}$ allows for wide operating voltage range
- Low gate charge



Absolute Maximum Ratings T_{A=25°C} unless otherwise noted

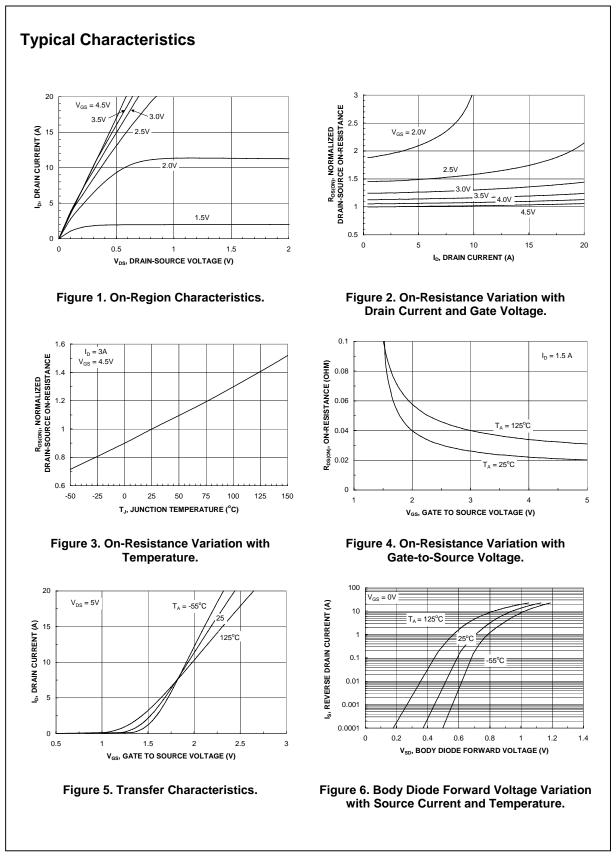
Symbol	Parameter			Ratings	Units
V _{DSS}	Drain-Source Voltage			20	
V _{GSS}	Gate-Source Voltage			±10	
ID	Drain Curren	t – Continuous	(Note 1a)	6.5	A
		– Pulsed		20	
P _D	Power Dissipation for Dual Operation			2	W
	Power Dissipation for Single Operation		ON (Note 1a)	1.6	
			(Note 1b)	1	
			(Note 1c)	0.9	
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	
Therma	I Charact	eristics			
R _{0JA}	Thermal Res	istance, Junction-to-Amb	Dient (Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)			40 °	
Packag	e Marking	and Ordering l	Information		
Device Marking		Device	Reel Size	Tape width	Quantity
FDS9926A		FDS9926A	13"	12mm	2500 units

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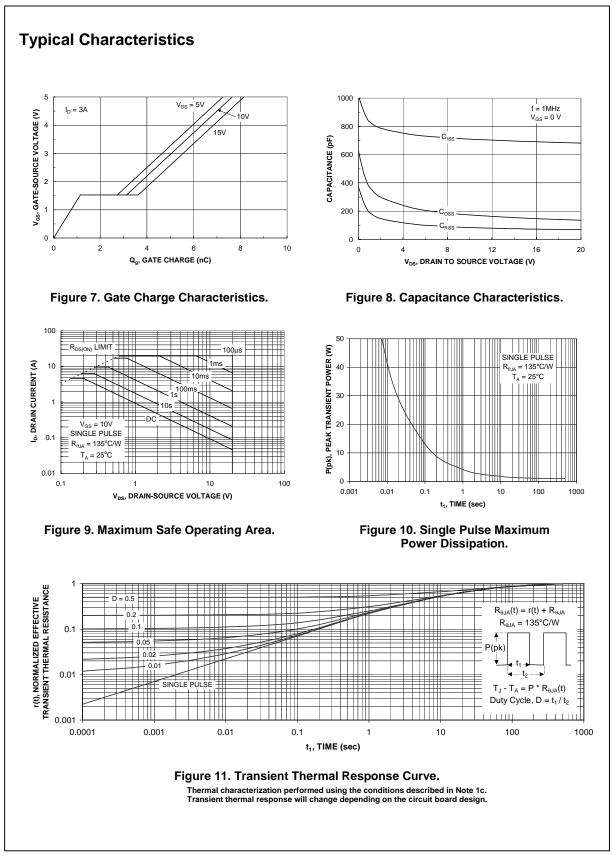
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Char	acteristics				l		
BV _{DSS}	Drain–Source Breakdown Voltag	$V_{GS} = 0 V, I_D = 250 \mu A$	20			V	
Δ <u>BV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		14		mV/°C	
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 16 V$, $V_{GS} = 0 V$			1	μA	
GSSF	Gate–Body Leakage, Forward	$V_{GS} = 8 V$, $V_{DS} = 0 V$			100	nA	
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -8 V$ $V_{DS} = 0 V$			-100	nA	
On Char	acteristics (Note 2)		I	1		1	
	acteristics (Note 2) Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	0.5	1	1.5	V	
$\Delta V_{GS(th)}$ ΔT_J	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		-3		mV/°C	
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{c} V_{GS}=4.5 \ V, I_{D}=6.5 \ A \\ V_{GS}=2.5 \ V, I_{D}=5.4 \ A \\ V_{GS}=4.5 \ V, \ I_{D}=6.5 A, \ T_{J}=125^{\circ} C \end{array}$		0.025 0.036 0.035	0.030 0.043 0.050	Ω	
D(on)	On–State Drain Current	$V_{GS} = 4.5 \text{ V}, \qquad V_{DS} = 5 \text{ V}$	15			А	
J FS	Forward Transconductance	$V_{DS} = 5 V$, $I_D = 3 A$		11		S	
Dvnamio	Characteristics						
C _{iss}	Input Capacitance	$V_{DS} = 10 V$, $V_{GS} = 0 V$,		700		pF	
Coss	Output Capacitance	f = 1.0 MHz		175	1	pF	
Crss	Reverse Transfer Capacitance			85	1	pF	
	g Characteristics (Note 2)		1				
d(on)	Turn–On Delay Time	$V_{DD} = 10 V$, $I_D = 1 A$,		8	16	ns	
	Turn–On Rise Time	$V_{\text{GS}} = 4.5 \text{ V}, \qquad \text{R}_{\text{GEN}} = 6 \Omega$		10	18	ns	
.d(off)	Turn-Off Delay Time			18	29	ns	
.f	Turn–Off Fall Time			5	10	ns	
, Qg	Total Gate Charge	$V_{DS} = 10 V$, $I_D = 3A$,		7	10	nC	
Q _{gs}	Gate–Source Charge	$V_{GS} = 4.5 V$		1.2		nC	
Q _{gd}	Gate–Drain Charge			1.9		nC	
	ource Diode Characteristic	s and Maximum Patings	I	1		L	
s	Maximum Continuous Drain–Sou				1.3	А	
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0$ V, $I_S = 1.3$ A (Note 2)		0.65	1.2	V	
		hermal resistance where the case thermal reference termined by the user's board design. $\varphi \wp \qquad \qquad$	\mathbf{r} is defined a	as the solde	er mounting	surface of	
	a) 78°/W when mounted on a 0.5in ² pad of 2 oz copper	b) 125°/W when hi mounted on a 0.02 i in ² pad of 2 oz ii copper c	(c)	c) 135°/W when mounted on a minimum pad.			

FDS9926A Rev D (W)

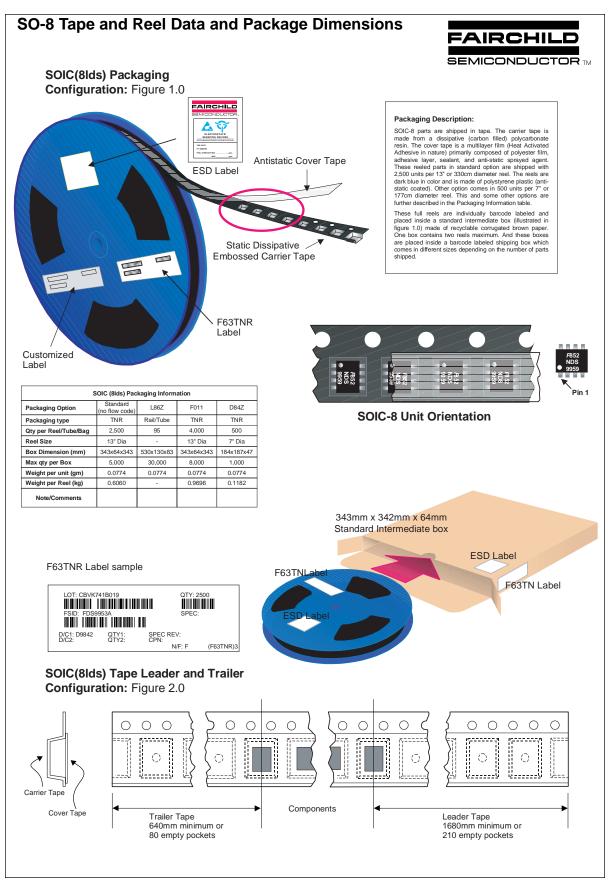


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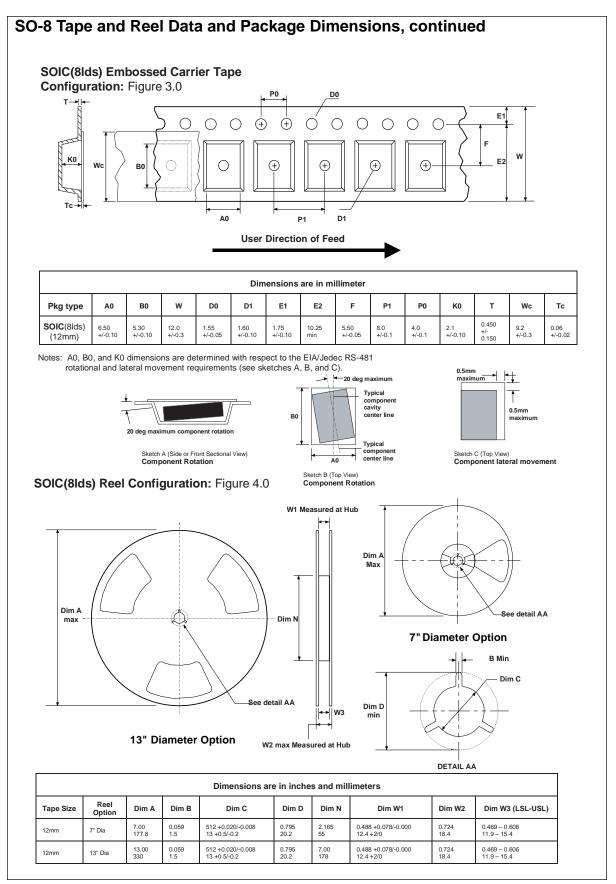


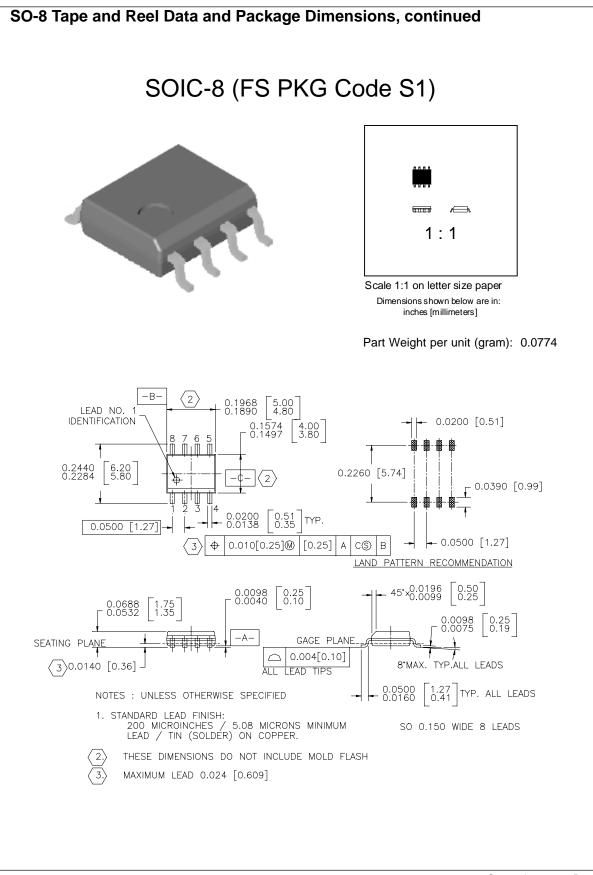
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July 1999, Rev. B





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